



P-Channel 12-V (D-S) MOSFET

PRODUCT SUMMARY

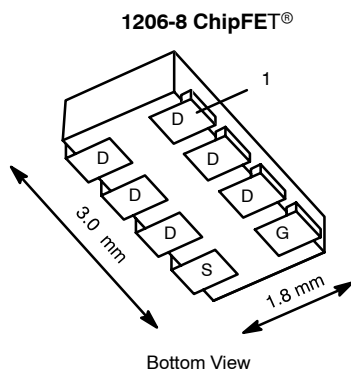
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
-12	0.027 @ $V_{GS} = -4.5$ V	-8.1
	0.0335 @ $V_{GS} = -2.5$ V	-7.3
	0.045 @ $V_{GS} = -1.8$ V	-6.3

FEATURES

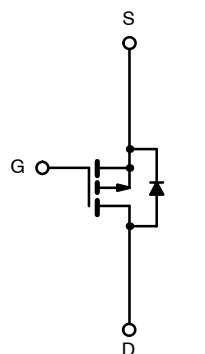
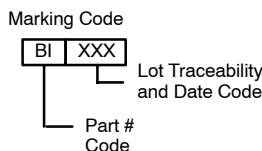
- TrenchFET® Power MOSFETS
- Low $r_{DS(on)}$ and Excellent Power Handling In Compact Footprint

APPLICATIONS

- Battery and Load Switch for Portable Devices



Ordering Information: Si5473DC-T1



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter		Symbol	5 secs	Steady State	Unit
Drain-Source Voltage		V _{DS}	-12		V
Gate-Source Voltage		V _{GS}	± 8		
Continuous Drain Current (T _J = 150°C) ^a	T _A = 25°C	I _D	-8.1	-5.9	A
	T _A = 85°C		-5.9	-4.3	
Pulsed Drain Current		I _{DM}	± 20		
Continuous Source Current ^a		I _S	-2.1	-1.1	
Maximum Power Dissipation ^a	T _A = 25°C	P _D	2.5	1.3	W
	T _A = 85°C		1.3	0.7	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150		°C
Soldering Recommendations (Peak Temperature) ^{b, c}			260		

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 5$ sec	R_{thJA}	40	50	$^\circ\text{C/W}$
	Steady State		80	95	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	15	20	

Notes

- Surface Mounted on 1" x 1" FR4 Board.
- See Reliability Manual for profile. The ChipFET is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

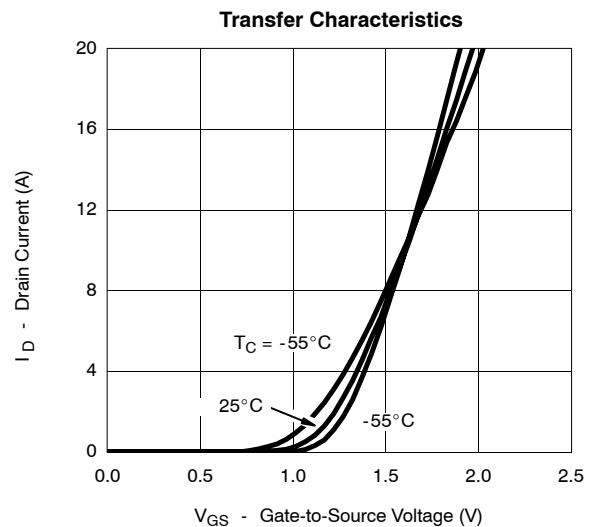
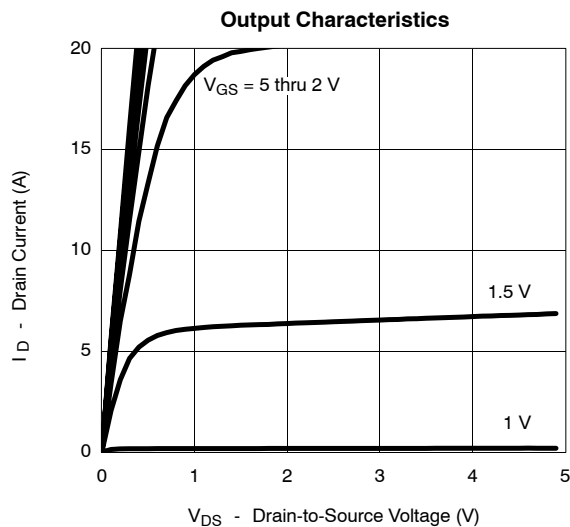
SPECIFICATIONS ($T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

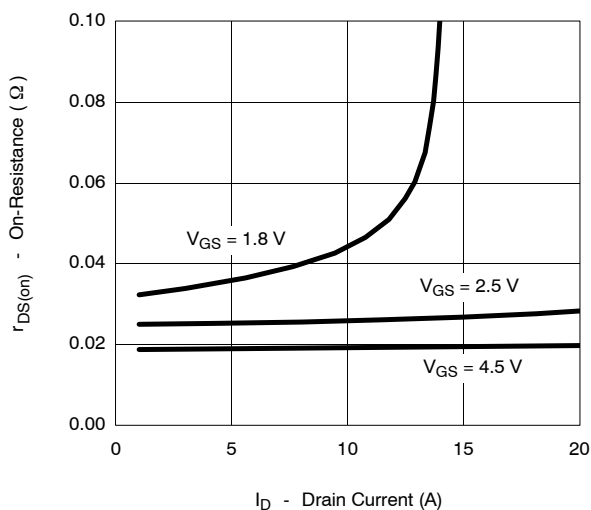
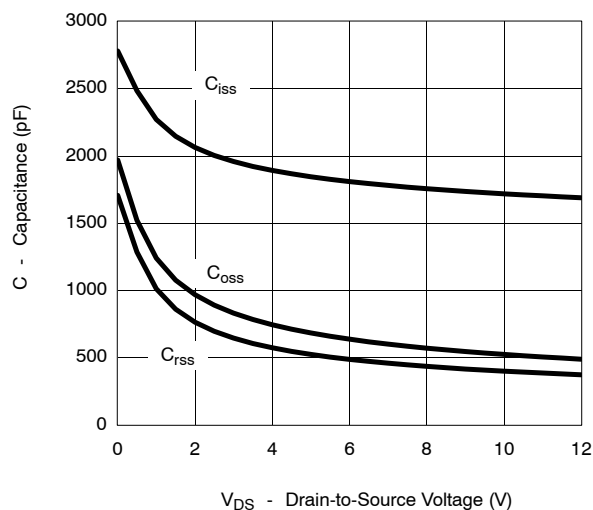
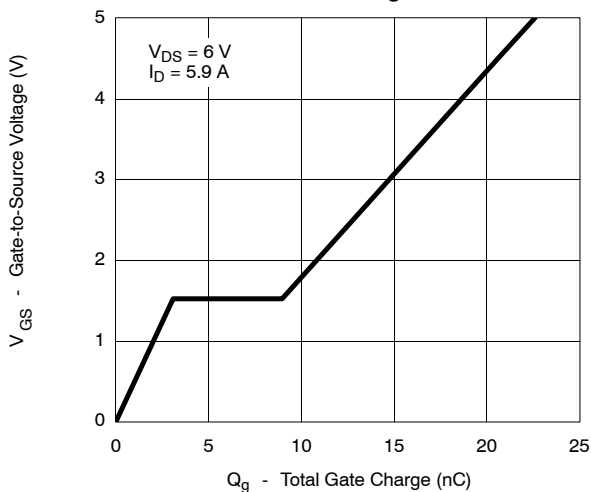
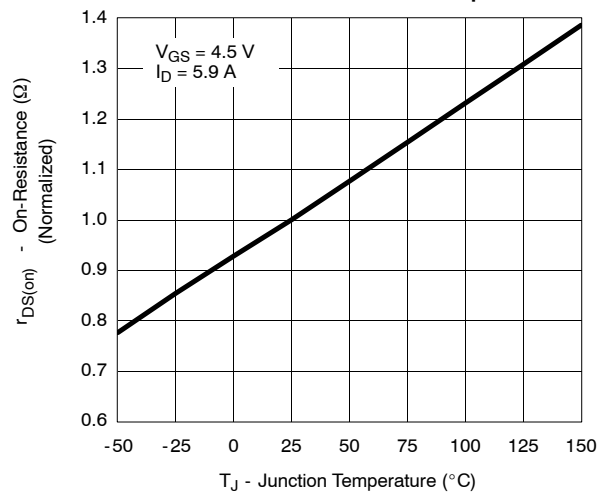
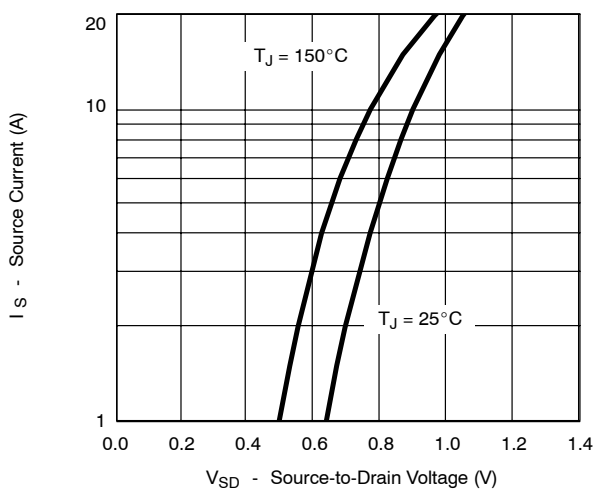
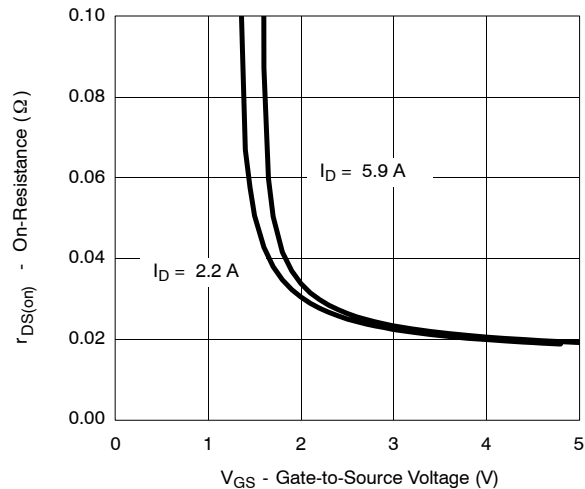
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	-0.40		-1.0	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\ \text{V}, V_{GS} = \pm 8\ \text{V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -9.6\ \text{V}, V_{GS} = 0\ \text{V}$			-1	μA
		$V_{DS} = -9.6\ \text{V}, V_{GS} = 0\ \text{V}, T_J = 85^\circ\text{C}$			-5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \leq -5\ \text{V}, V_{GS} = -4.5\ \text{V}$	-20			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = -4.5\ \text{V}, I_D = -5.9\ \text{A}$		0.022	0.027	Ω
		$V_{GS} = -2.5\ \text{V}, I_D = -5.3\ \text{A}$		0.028	0.0335	
		$V_{GS} = -1.8\ \text{V}, I_D = -2.2\ \text{A}$		0.036	0.045	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -5\ \text{V}, I_D = -5.9\ \text{A}$		20		S
Diode Forward Voltage ^a	V_{SD}	$I_S = -1.1\ \text{A}, V_{GS} = 0\ \text{V}$		-0.8	-1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = -6\ \text{V}, V_{GS} = -4.5\ \text{V}, I_D = -5.9\ \text{A}$		21	32	nC
Gate-Source Charge	Q_{gs}			3.1		
Gate-Drain Charge	Q_{gd}			6.0		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -6\ \text{V}, R_L = 6\ \Omega$ $I_D \cong -1\ \text{A}, V_{GEN} = -4.5\ \text{V}, R_G = 6\ \Omega$		25	40	ns
Rise Time	t_r			50	75	
Turn-Off Delay Time	$t_{d(off)}$			145	220	
Fall Time	t_f			90	135	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = -1.1\ \text{A}, di/dt = 100\ \text{A}/\mu\text{s}$		70	105	

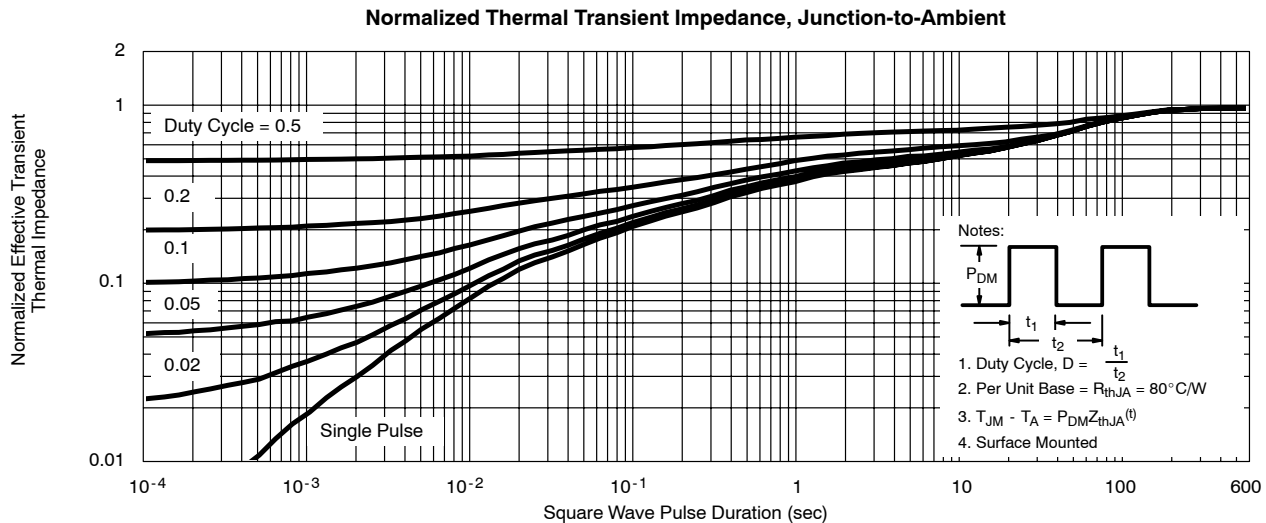
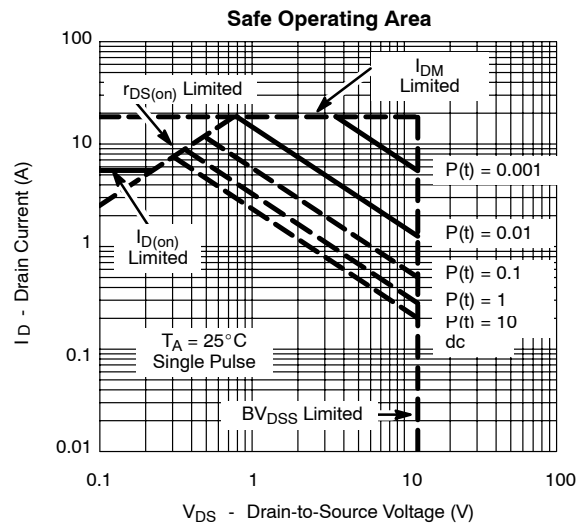
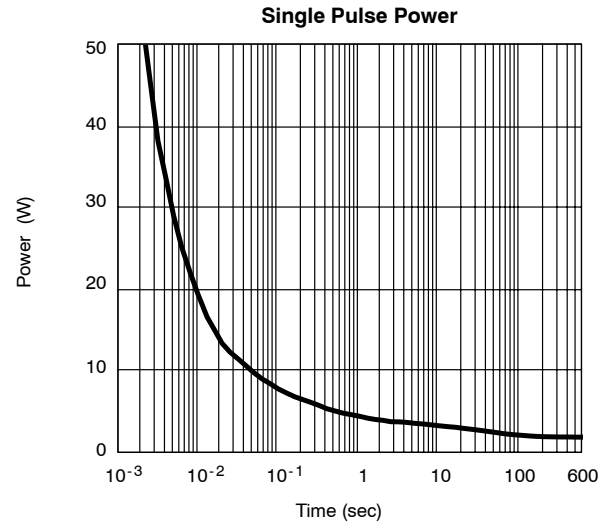
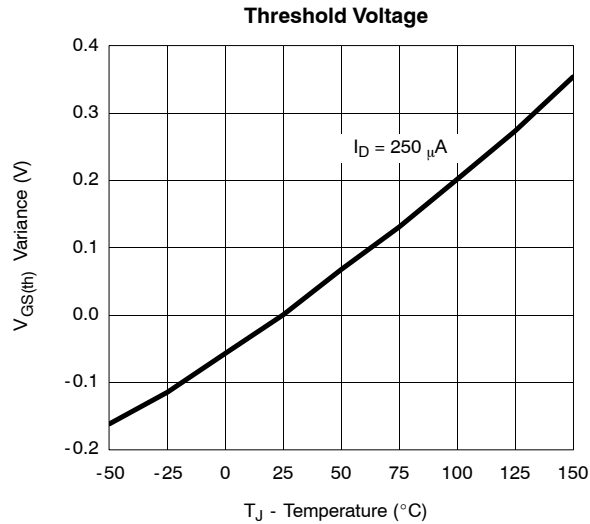
Notes

a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

b. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

**TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)****On-Resistance vs. Drain Current****Capacitance****Gate Charge****On-Resistance vs. Junction Temperature****Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage**

TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)




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